ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESD7382MUT5G

The ESD7382 is designed to protect voltage sensitive components that require ultra−low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Features

- Ultra−Low Capacitance: 0.37 pF
- Low Clamping Voltage
- Small Body Outline Dimensions: 0.60 mm x 0.30 mm
- Low Body Height: 0.3 mm
- Stand−off Voltage: 5.0 V
- Low Leakage
- Insertion Loss: 0.030 dBm
- Response Time is < 1 ns
- Low Dynamic Resistance < 1 Ω
- IEC61000−4−2 Level 4 ESD Protection
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

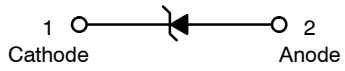
Typical Applications

- GPIO and Power Line Protection

MAXIMUM RATINGS

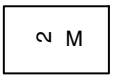
Rating		Symbol	Value	Unit
IEC 61000−4−2 (ESD)	Contact Air		±20 ±20	kV
Total Power Dissipation on FR−5 Board (Note 1) @ T_A = 25°C		P_D	250	mW
Thermal Resistance, Junction−to−Ambient		$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range		T_J, T_{stg}	−40 to +125	°C
Lead Solder Temperature − Maximum (10 Second Duration)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR−5 = 1.0 x 0.75 x 0.62 in.



MARKING DIAGRAM

X3DFN2
CASE 152AF



2 = Specific Device Code (Rotated 270°)
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
ESD7382MUT5G	X3DFN2 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

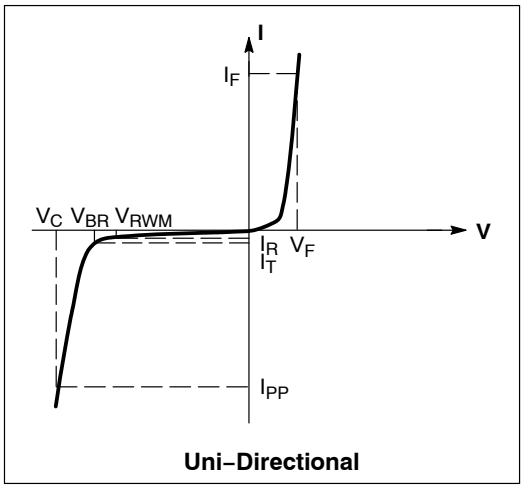
See Application Note AND8308/D for further description of survivability specs.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



Uni−Directional

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				5.0	V
Breakdown Voltage (Note 2)	V_{BR}	I_T = 1 mA	5.2			V
Reverse Leakage Current	I_R	V_{RWM} = 5.0 V			1.0	μA
Clamping Voltage (Note 3)	V_C	I_{PP} = 1 A			8.0	V
Clamping Voltage (Note 3)	V_C	I_{PP} = 3 A			10	V
ESD Clamping Voltage	V_C	Per IEC61000−4−2	See Figures 1 and 2			
Junction Capacitance	C_J	V_R = 0 V, f = 1 Mhz V_R = 0 V, f < 1 GHz		0.37 0.25	0.55 0.55	pF
Dynamic Resistance	R_{DYN}	TLP Pulse		0.32		Ω
Insertion Loss		f = 1 Mhz f = 8.5 GHz		0.030 0.573		dB

2. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
3. Non−repetitive current pulse at T_A = 25°C, per IEC61000−4−5 waveform.

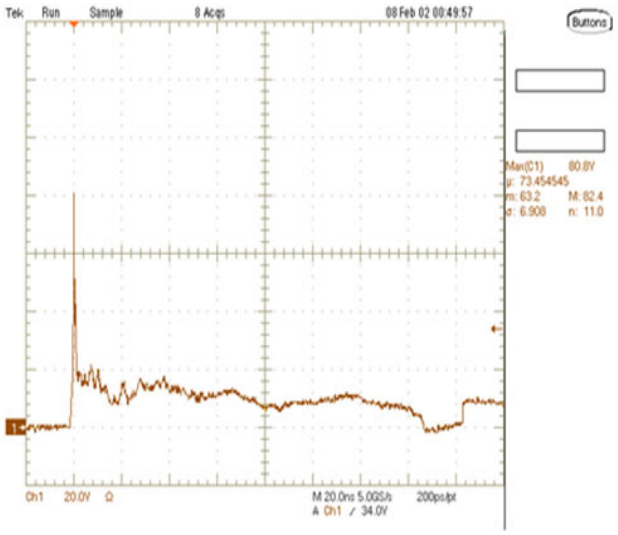


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000−4−2

Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000−4−2

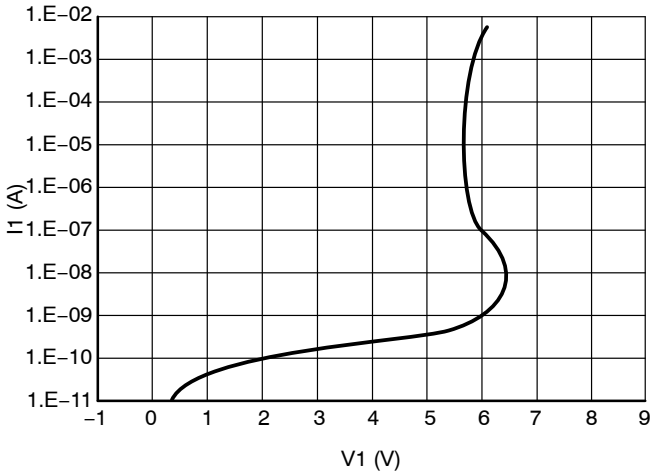


Figure 3. IV Characteristics

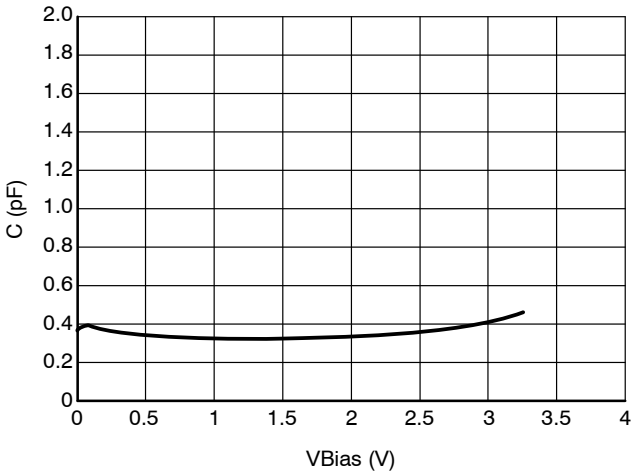


Figure 4. CV Characteristics

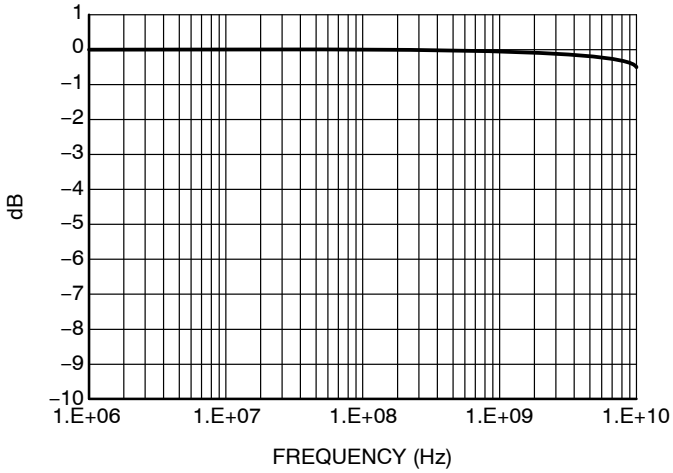


Figure 5. RF Insertion Loss

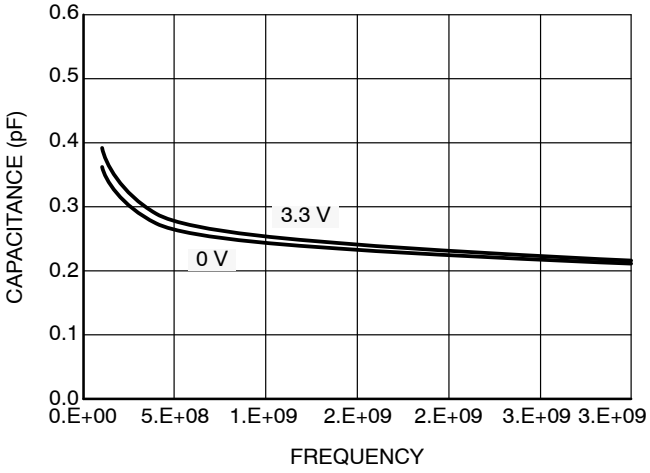


Figure 6. Capacitance over Frequency

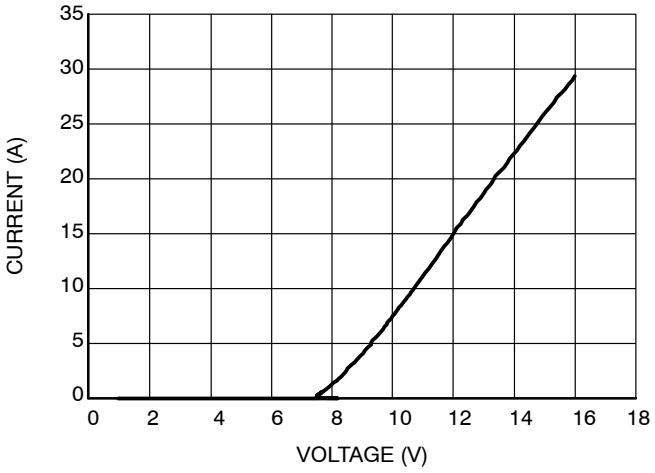


Figure 7. Positive TLP I−V Curve

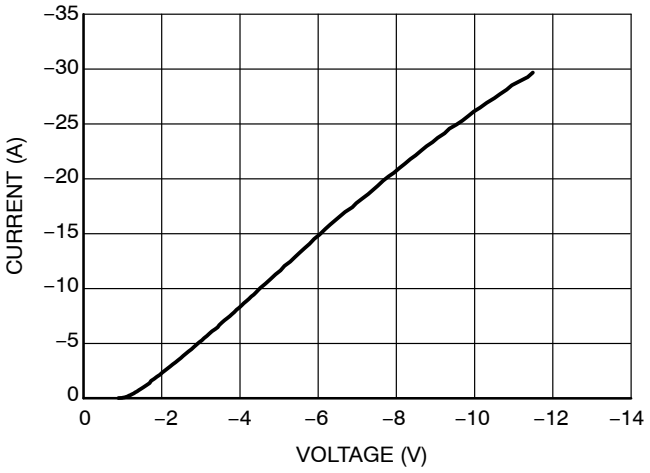


Figure 8. Negative TLP I−V Curve

IEC 61000−4−2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

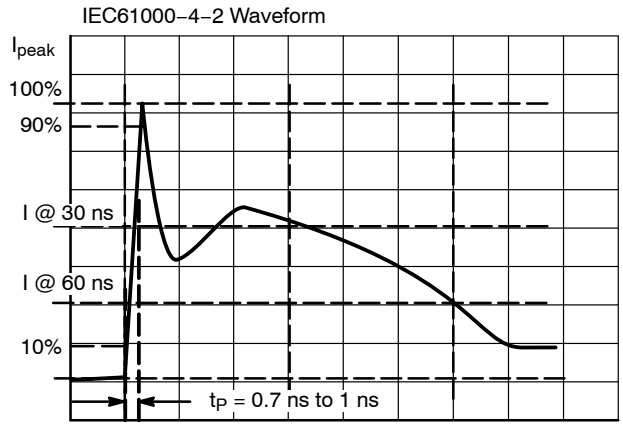


Figure 9. IEC61000−4−2 Spec

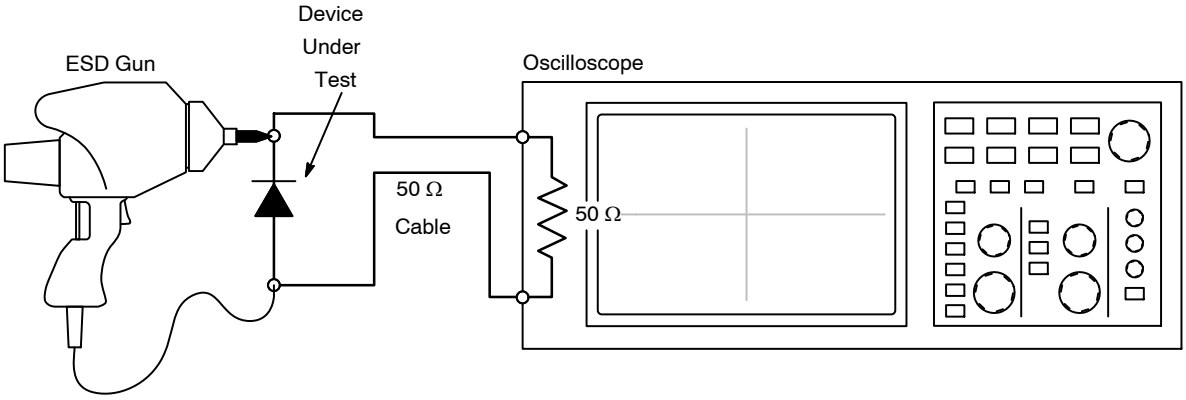


Figure 10. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000−4−2 waveform. Since the IEC61000−4−2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. **onsemi** has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how **onsemi** creates these screenshots and how to interpret them please refer to AND8307/D.

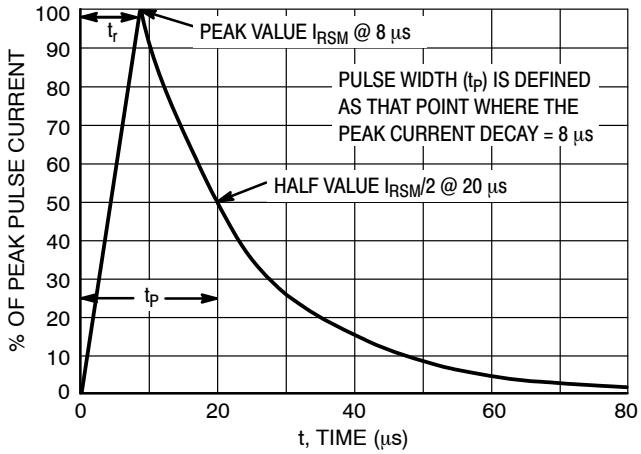
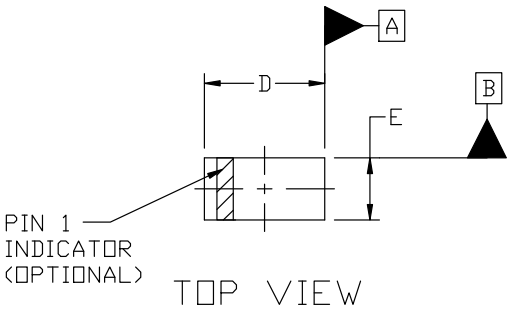


Figure 11. 8 X 20 μs Pulse Waveform

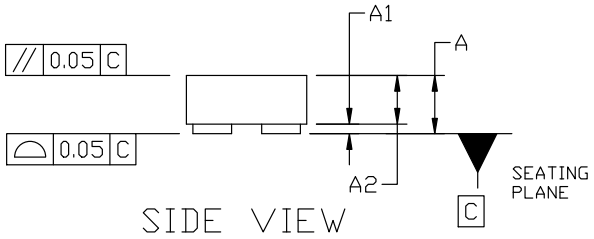
ESD7382MUT5G

PACKAGE DIMENSIONS

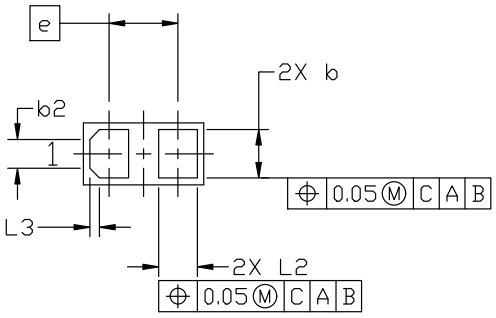
X3DFN2 0.62x0.32x0.24, 0.35P
CASE 152AF
ISSUE C



TOP VIEW



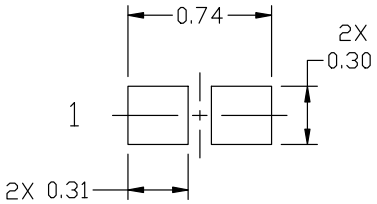
SIDE VIEW



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 0201

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.25	0.29	0.33
A1	0.00	---	0.05
A2	0.14	0.24	0.34
b	0.22	0.25	0.28
b2	0.150 REF		
D	0.58	0.62	0.66
E	0.28	0.32	0.36
e	0.355 BSC		
L2	0.17	0.20	0.23
L3	0.050 REF		



RECOMMENDED
MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

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